

Discrete POWER & Signal **Technologies**

2N5962



MMBT5962



NPN General Purpose Amplifier

This device is designed for use as low noise, high gain, general purpose amplifiers requiring collector currents to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units | |
|-----------------------------------|--|-------------|-------|--|
| V _{CEO} | Collector-Emitter Voltage | 45 | V | |
| V _{CBO} | Collector-Base Voltage | 45 | V | |
| V _{EBO} | Emitter-Base Voltage | 8.0 | V | |
| l _c | Collector Current - Continuous | 100 | mA | |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C | |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

| Symbol | Characteristic | Мах | | Units |
|-------------------|---|--------|-----------|-------|
| | | 2N5962 | *MMBT5962 | |
| P _D | Total Device Dissipation | 625 | 350 | mW |
| | Derate above 25°C | 5.0 | 2.8 | mW/°C |
| $R_{\theta_{JC}}$ | Thermal Resistance, Junction to Case | 83.3 | | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 200 | 357 | °C/W |

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

© 1997 Fairchild Semiconductor Corporation

NPN General Purpose Amplifier (continued)

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|----------------------|---|--|------------|-----------|----------|
| | | | | | - |
| | RACTERISTICS | | | | |
| / _{(BR)CEO} | Collector-Emitter Breakdown Voltage* | $I_{\rm C} = 5.0 \text{ mA}, I_{\rm B} = 0$ | 45 | | V |
| / _{(BR)CBO} | Collector-Base Breakdown Voltage | $I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$ | 45 | | V |
| (BR)EBO | Emitter-Base Breakdown Voltage | $I_{\rm E} = 10 \ \mu {\rm A}, I_{\rm C} = 0$ | 8.0 | | V |
| СВО | Collector Cutoff Current | $V_{CB} = 30 \text{ V}, I_E = 0$ | | 2.0 | nA |
| EBO | Emitter Cutoff Current | $V_{CB} = 30 \text{ V}, \text{ I}_{E} = 0, \text{ T}_{A} = 65 ^{\circ}\text{C}$ $V_{EB} = 5.0 \text{ V}, \text{ I}_{C} = 0$ | | 50 1.0 | nA nA |
| -00 | | | | | |
| ON CHAR | ACTERISTICS* | | | | |
| FE | DC Current Gain | $V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}$ | 450 | | |
| | | $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ | 500 | | |
| | | $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ | 550 600 | 1400 | |
| / _{CE(sat)} | Collector-Emitter Saturation Voltage | $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$ | 000 | 0.2 | V |
| / _{BE(on)} | Base-Emitter On Voltage | $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ | 0.5 | 0.7 | V |
| SMALL S | IGNAL CHARACTERISTICS | | | | |
| Ccb | Collector-Base Capacitance | V _{CB} = 5.0 V | | 4.0 | pF |
| eb | Emitter-Base Capacitance | V _{EB} = 0.5 V | | 6.0 | pF |
| fe | Small-Signal Current Gain | $I_{\rm C} = 10 \text{ mA}, V_{\rm CE} = 5.0 \text{ V},$ | | | |
| | | f = 1.0 kHz I _C = 10 mA, V _{CE} = 5.0 V, | 600 | 200 | |
| | | f = 100 MHz | 1.0 | | |
| ١F | Noise Figure | $V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A},$ | | | |
| | | $R_s = 10 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz},$ $B_w = 400 \text{ Hz}$ | | 3.0 | dB |
| | | $V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A},$ | | 0.0 | 42 |
| | | $R_s = 1.0 \text{ k}\Omega$, f = 1.0 kHz, | | 6.0 | ٩D |
| | | $B_W = 400 \text{ Hz}$ $V_{CF} = 5.0 \text{ V}, I_C = 100 \mu\text{A},$ | | 6.0 | dB |
| | | $R_s = 10 \text{ k}\Omega$, f = 1.0 kHz, | | | |
| | | $B_{W} = 400 \text{ Hz}$ | | 4.0 | dB |
| | | $V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A},$ $R_S = 100 k\Omega, f = 1.0 k\text{Hz},$ | | | |
| | | $B_W = 400 \text{ Hz}$ | | 8.0 | dB |
| | | $V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu \text{A},$ | | | |
| | | $R_{s} = 10 \text{ k}\Omega$, f = 10 Hz -10 kHz $B_{W} = 15.7 \text{ kHz}$ | | 3.0 | dB |
| *Pulso Tost | : Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0% | | | | |
| | 1 also main 2 000 µ0, Daty Oyolo 22.070 | | | | |
| | | | | | |
| | | | | | |
| | | | | | |
| | | | | | |

-_ 2N5962/ MMBT5962



©2001 Fairchild Semiconductor Corporation

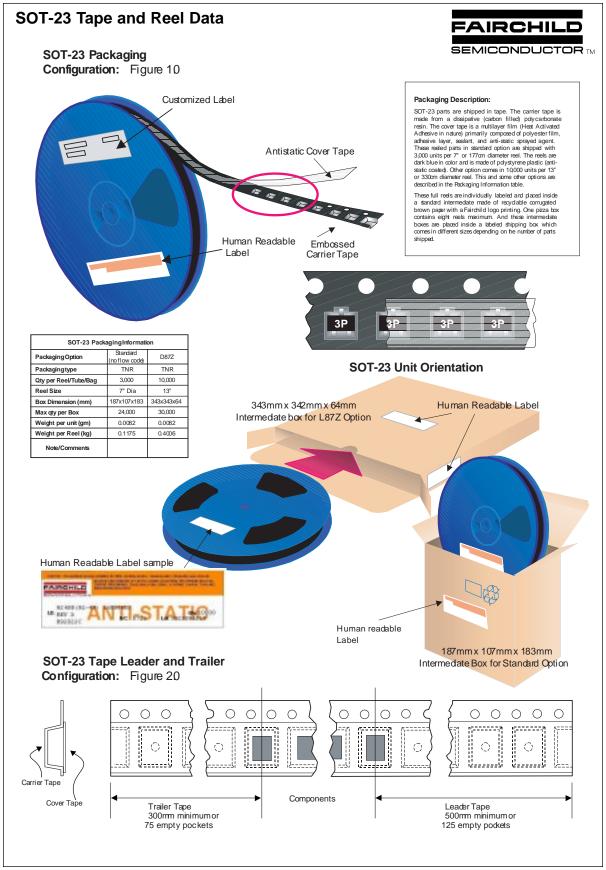
March 2001, Rev. B1





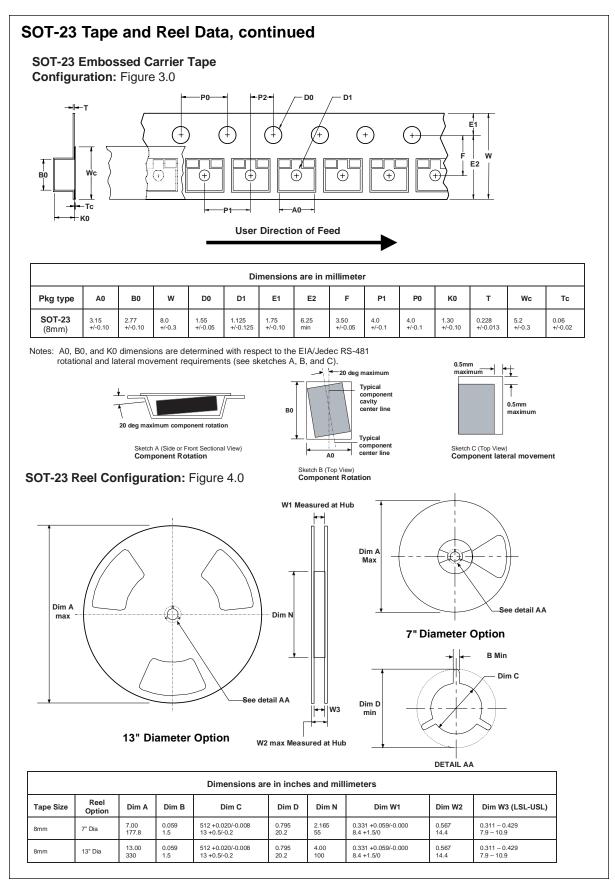
July 1999, Rev. A



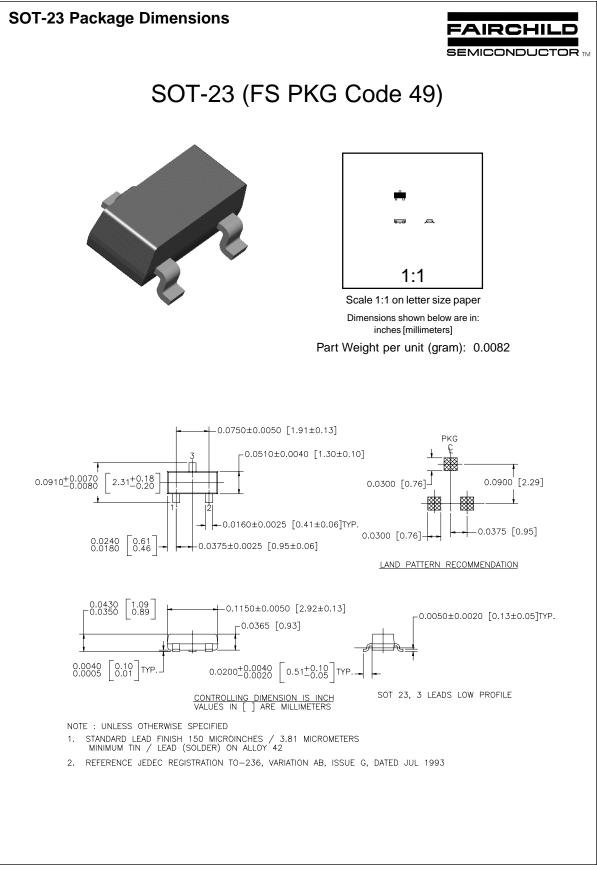


©2000 Fairchild Semiconductor International

September 1999, Rev. C



September 1999, Rev. C



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™ Bottomless™ CoolFET™ CROSSVOLT™ DOME™ E²CMOS[™] EnSigna™ FACT™ FACT Quiet Series[™] FAST[®]

FASTr™ GlobalOptoisolator™ GTO™ HiSeC™ **ISOPLANAR™** MICROWIRE™ OPTOLOGIC™ **OPTOPLANAR™** PACMAN™ POP™

PowerTrench[®] QFET™ QS™ QT Optoelectronics[™] Quiet Series[™] SILENT SWITCHER® SMART START™ SuperSOT[™]-3 SuperSOT[™]-6 SuperSOT[™]-8

SyncFET™ TinyLogic™ UHC™ VCX™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

| Datasheet Identification | Product Status | Definition |
|--------------------------|---------------------------|---|
| Advance Information | Formative or In Design | This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. |
| Preliminary | First Production | This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design. |
| No Identification Needed | Full Production | This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design. |
| Obsolete | Not In Production | This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only. |
| | 1 | Rev G |

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor: